

Assignment - 2

Group - 6

Section - B

Group Members :

1. Abdullah-Al-Sheak Jaber (201714014)
2. Ayon Roy (201714018)
3. Dipan Sadekeen Uday (201714020)

$$\begin{aligned} X &= (14 + 18 + 20) \bmod 3 \\ &= 52 \bmod 3 \\ &= 1 \end{aligned}$$

$$\begin{aligned} Y &= \text{Cube}(x) \bmod 6 + 1 \\ &= 1^3 \bmod 6 + 1 \\ &= 2 \end{aligned}$$

$$\begin{aligned} Z &= (X + 3 * Y) \bmod 5 + 1 \\ &= (1 + 3 * 2) \bmod 5 + 1 \\ &= 2 + 1 \\ &= 3 \end{aligned}$$

Ans to the question no. 1

Given, $\frac{w_1}{L_1} = Y$

$$k = 6$$

$$C_{out} = (0.10 + 2) \text{ pF}$$

$$\therefore \frac{w_1}{L_1} = 2$$

$$C_{out} = (0.10 + 3) \text{ pF} \\ = 3.10 \text{ pF}$$

we know,

$$k = \left(\frac{w_1}{L_1} \right) / \left(\frac{w_2}{L_2} \right)$$

$$\Rightarrow \frac{w_2}{L_2} = \left(\frac{w_1}{L_1} \right) / k$$

$$\Rightarrow \frac{w_2}{L_2} = 2/6$$

$$\therefore \frac{w_2}{L_2} = \frac{1}{3}$$

We know, the rise time of a NMOS inverter with depletion transistor load is,

$$t_n = \frac{60 C_{out}}{w_2/L_2} \text{ ns}$$

$$\text{So, } t_n = \frac{60 \times 3.10}{\frac{1}{3}} \text{ ns}$$

$$= 60 \times 3.10 \times 3$$

$$= 558 \text{ ns}$$

$$\text{fall time, } t_f = \frac{35 C_{out}}{w_1/L_1}$$

$$= \frac{35 \times 3.10}{2}$$

$$= 54.25 \text{ ns}$$

Maximum frequency of the inverter circuit is,

$$f_{max} = \frac{1}{t_n + t_f}$$

$$= \frac{1}{558 + 54.25} \text{ GHz}$$

$$= 1.63 \times 10^{-3} \text{ GHz}$$

$$\therefore f_{max} = 1.63 \text{ MHz}$$

Ans to the question no. 2

Given,

$$\text{Nmos: } \epsilon \mu_n / D = 24 + 2 * (n+1) \text{ } \mu\text{A/V}^2$$

$$w_1 / L_1 = 1$$

$$V_{tn} = 1\text{V}$$

$$\text{pmos: } \epsilon \mu_p / D = 0.5 * \epsilon \mu_n / D \text{ } \mu\text{A/V}^2$$

$$w_2 / L_2 = 2$$

$$V_{tp} = 1\text{V}$$

So,

$$\begin{aligned} \text{Nmos: } \epsilon \mu_n / D &= 24 + 2 * (1+1) \text{ } \mu\text{A/V}^2 \\ &= 28 \text{ } \mu\text{A/V}^2 \end{aligned}$$

$$\begin{aligned} \text{pmos: } \epsilon \mu_p / D &= 0.5 * 28 \text{ } \mu\text{A/V}^2 \\ &= 14 \end{aligned}$$

For Transistor T_1 (NMOS):

$$I_{ds1} = \frac{\epsilon \mu n}{D} \times \frac{w_i}{L_1} \times \frac{(V_{gs} - V_{tn})^2}{2}$$

$$= 28 \times 1 \times \frac{(V_{gs} - V_{tn})^2}{2}$$

$$= 14 \times (V_{gs} - 1)^2 \times 1 =$$

$$V_{in} = V_{gs}$$

$$V_{out} = V_{ds}$$

$$V_{ds} = V_{gs} - V_t$$

$$V_{gs} - 2V = 0.2V \leftarrow$$

$$V_{gs} - 1V = 0.2V \leftarrow$$

$$V_{gs} - 2 = 0.2V \leftarrow$$

V_{gs}	V_{in}	Pinchoff, $V_{ds} = V_{gs} - V_t$	$I_{ds} = 14(V_{gs} - 1)^2$	$V_{out} = V_{ds}$
2	2	1	$14 - 0.4 = 0.2V \leftarrow$	1
2.5	2.5	1.5	$31.5 - 0.4 = 0.2V \leftarrow$	1.5
3	3	2	56	2
4	4	3	126	3
5	5	4	224	4

For Transistor T_2 (pmos)

$$I_{ds_2} = \frac{\epsilon \mu_p}{D} \times \frac{W_2}{L_2} \times \frac{(V_{sg} - V_{tp})^2}{2}$$

$$= 14 \times 2 \times \frac{(V_{sg} - 1)^2}{2}$$

$$= 14 \times (V_{sg} - 1)^2$$

$$\Rightarrow V_{sg} = V_s - V_g$$

$$\Rightarrow V_{sg} = V_p - V_{in}$$

$$\therefore V_{in} = 5 - V_{sg}$$

$$\Rightarrow V_{sd} = V_p - V_{out}$$

$$\therefore V_{out} = V_p - V_{sd}$$

$$V_{sd} = V_{sg} - V_{tp}$$

V_{sg}	V_{in}	Pinchoff, $V_{sd} = V_{sg} - V_p$	$I_{sd} = 14(V_{sg} - 1)^2$	$V_{out} = V_p - V_{sd}$
2	3	1	14	4
2.5	2.5	1.5	31.5	3.5
3	2	2	5.6	3
4	1	3	1.26	2
5	0	4	22.4	1

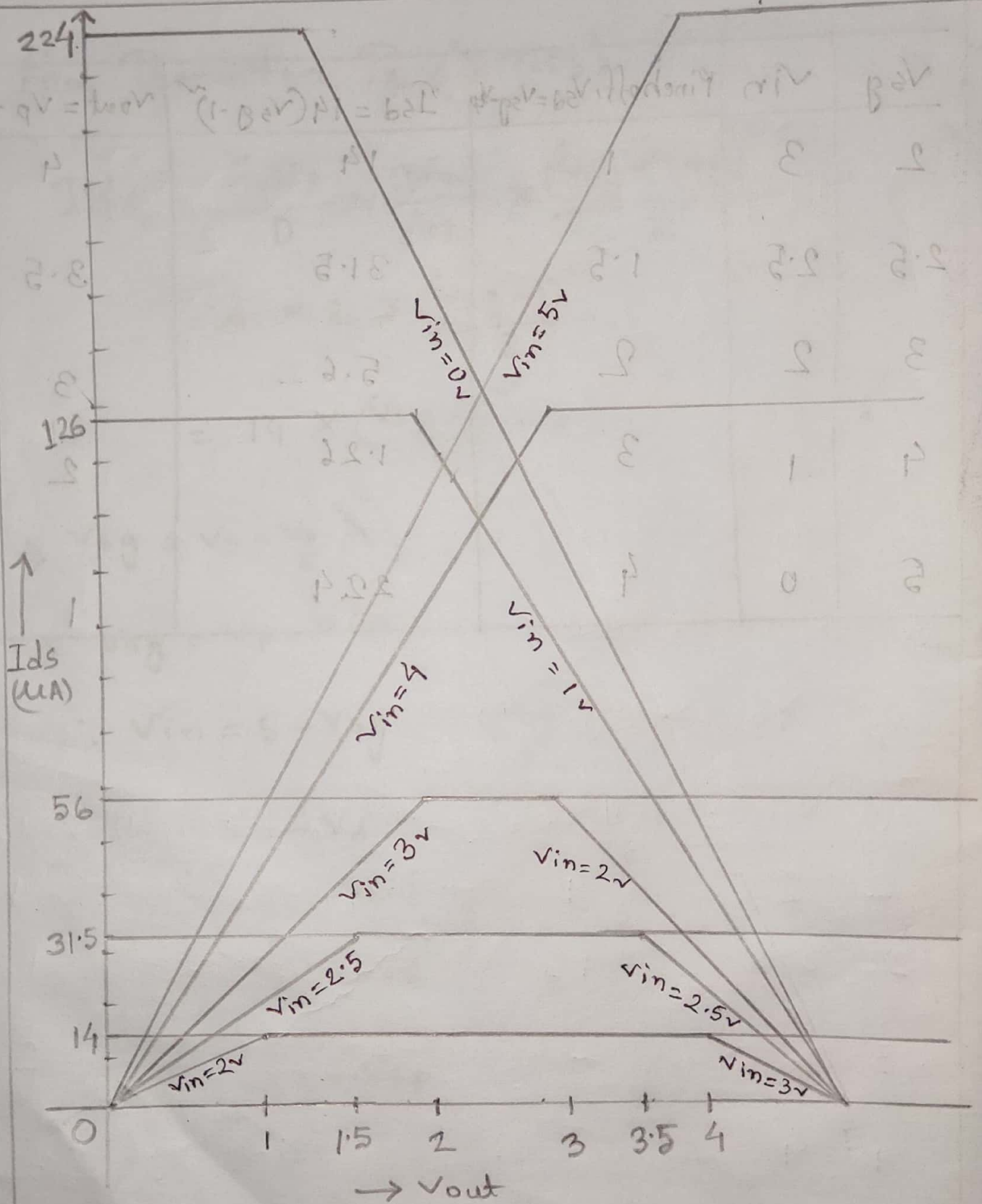


fig: I vs V_{out} charastie curve
for cmos inverter

To get the power graph we can calculate using the information from I vs V_{out} graph.

V_{in}	V_{out}	I
0	5	0
1	5	0
2	4.5	14
2.5	1.5 to 3.5	31.5
3	0.5	14
4	0	0
5	0	0

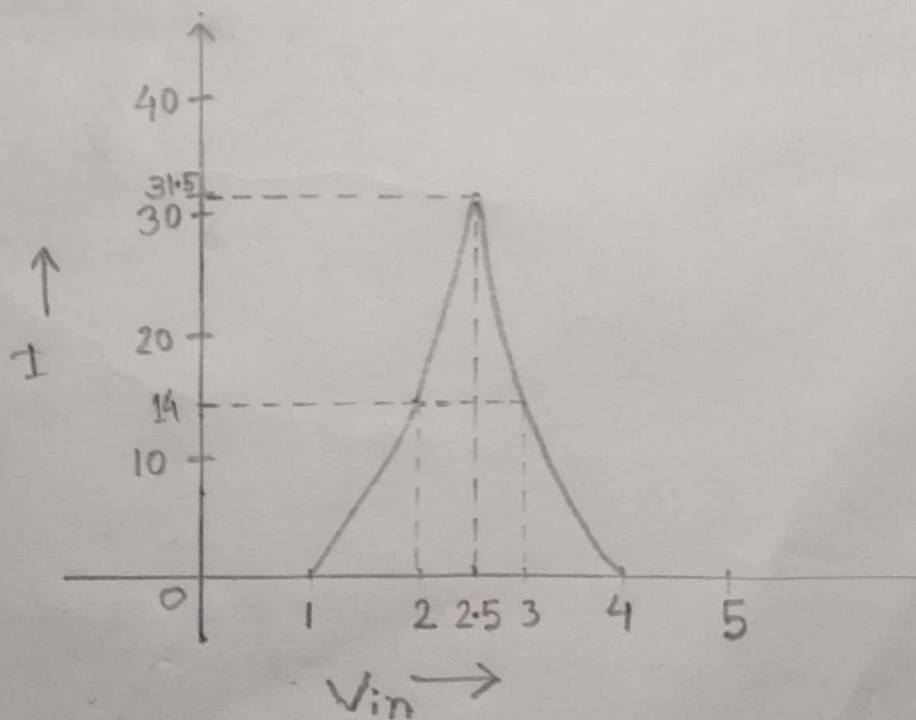


Fig: Power curve (I vs V_{in}) For CMOS Inverter